

ABSTRACT OF THE DISCLOSURE

A plasma processing method for processing a surface of an object to be processed made of a metal or a semiconductor by applying activated particles generated by a microplasma generated at a pressure of not lower than 10,000 Pa and not higher than three atmospheric pressures to the surface of the object, the method includes removing a natural oxide film on the surface of the object, and etching a part or whole of a region in which the natural oxide film has been removed.